SSC8229GS6

P-Channel Enhancement Mode MOSFET

➢ Features

V_{DS}	V_{GS}	$R_{DS(ON)}$ Typ.	I_D
-20V	±12V	22mΩ@-4V5	-5A
		29mΩ@-2V5	
		40mΩ@-1V8	

➢ Description

The SSC8229GS6 is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent RDSON with low gate charge. This device is suitable for use in load switch, electronic cigarette and Battery Isolation.

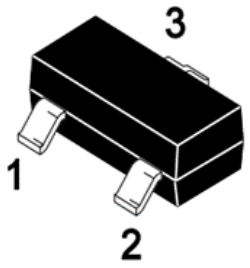
➢ Applications

- Load Switch
- Electronic Cigarette
- Battery Isolation

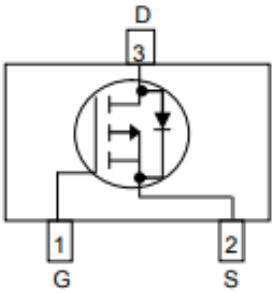
➢ Ordering Information

Device	Package	Shipping
SSC8229GS6	SOT-23	3000/Reel

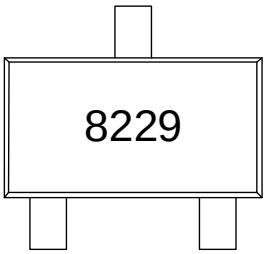
➢ Pin configuration



SOT-23



Pin Configuration (Top View)



Marking

➢ Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain-to-Source Voltage	-20	V
V_{GSS}	Gate-to-Source Voltage	±12	V
I_D	Continuous Drain Current [a]	-5	A
I_{DM}	Pulsed Drain Current [b]	-20	A
P_D	Power Dissipation [c]	0.89	W
P_{DSM}	Power Dissipation [a]	0.54	W
T_J	Operation junction temperature	-55~150	℃
T_{STG}	Storage temperature range	-55~150	℃

➢ Thermal Resistance Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance [a]	230	℃/W
$R_{\theta JC}$	Junction-to-Case Thermal Resistance	140	

Note:

a. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2oz.copper, in a still air environment with T_A=25℃.The value in any given application depends on the user is specific board design. The power dissipation is based on the t≤10s thermal resistance rating.

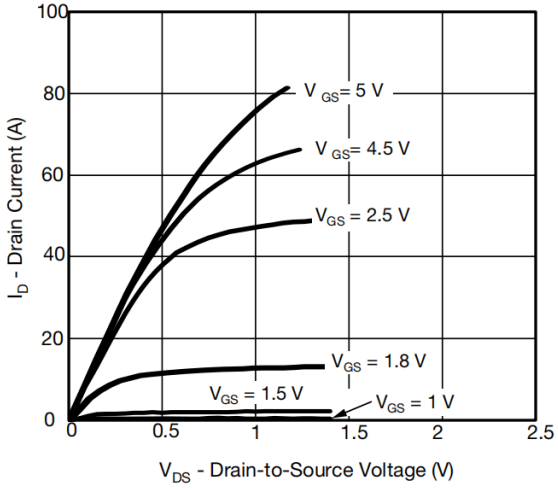
b. Repetitive rating, pulse width limited by junction temperature.

c. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

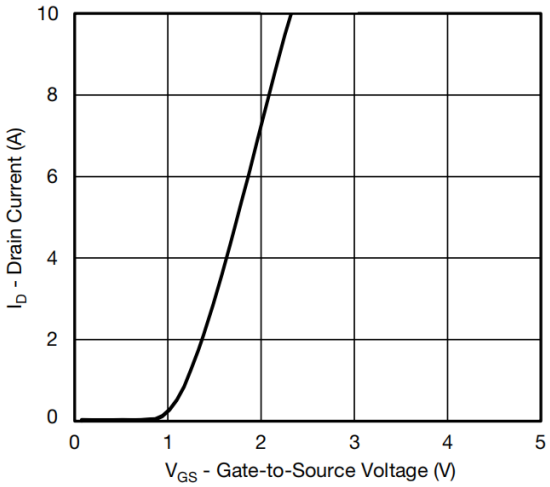
➢ Electrical Characteristics (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250uA	-0.4	-0.7	-1	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = -4.5V, I_D = -5A		22	28	mΩ
		V_{GS} = -2.5V, I_D = -3A		29	38	
		V_{GS} = -1.8V, I_D = -2A		40	55	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -16V, V_{GS} = 0V			-1	μA
Gate-Source Leak Current	I_{GSS}	V_{GS} = ±12V, V_{DS} = 0V			±100	nA
Transconductance	G_{FS}	V_{DS} = -5V, I_D = -2A		26		s
Forward Voltage	V_{SD}	V_{GS} = 0V, I_S = -2A			-1.3	V
Input Capacitance	C_{ISS}	V_{DS} = -10V, V_{GS} = 0V, f = 1MHz		1963		pF
Output Capacitance	C_{OSS}			207		
Reverse Transfer Capacitance	C_{RSS}			204		
Turn-on Delay Time	$T_{D(ON)}$	V_{GS} = -4.5V, V_{DS} = -10V, R_L = 3Ω, R_G = 6Ω		38		ns
Rise Time	T_r			29		
Turn-off Delay Time	$T_{D(OFF)}$			141		
Fall Time	T_f			84		
Total Gate Charge	Q_G	V_{GS} = -4.5V, V_{DS} = -15V, I_D = -4A		22		nC
Gate to Source Charge	Q_{GS}			4		
Gate to Drain Charge	Q_{GD}			4.5		

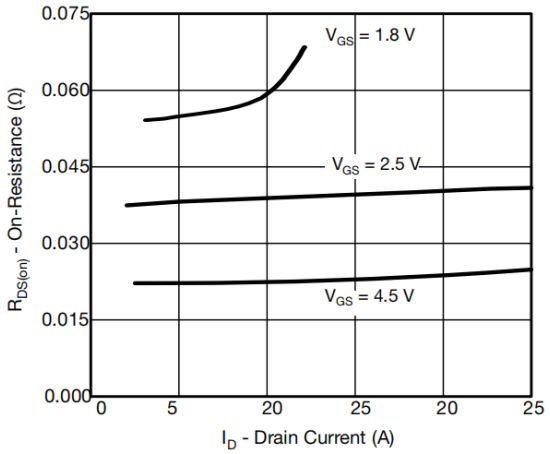
➢ Typical Performance Characteristics (T_A=25℃ unless otherwise noted)



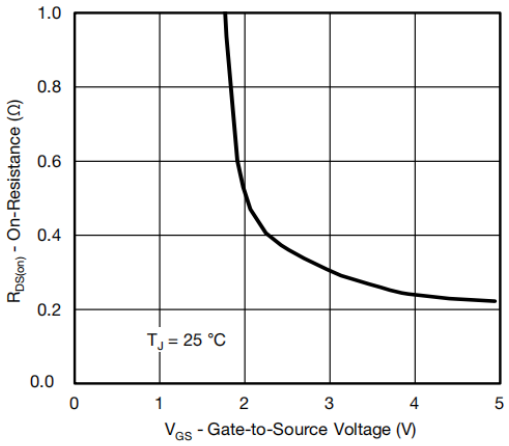
Output Characteristics



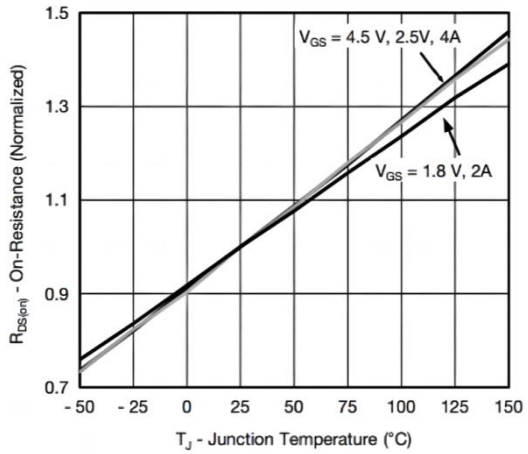
Transfer Characteristics



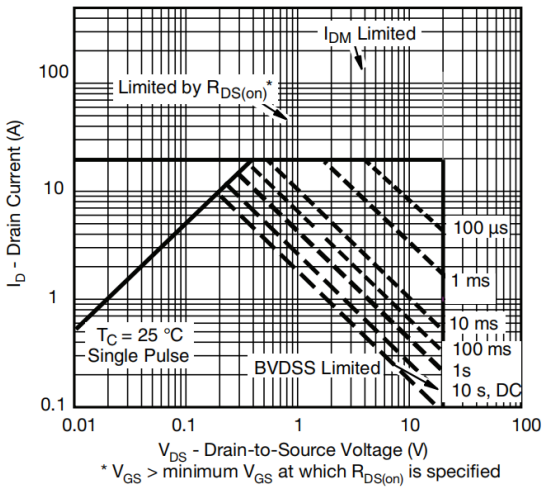
On-Resistance vs. Drain Current



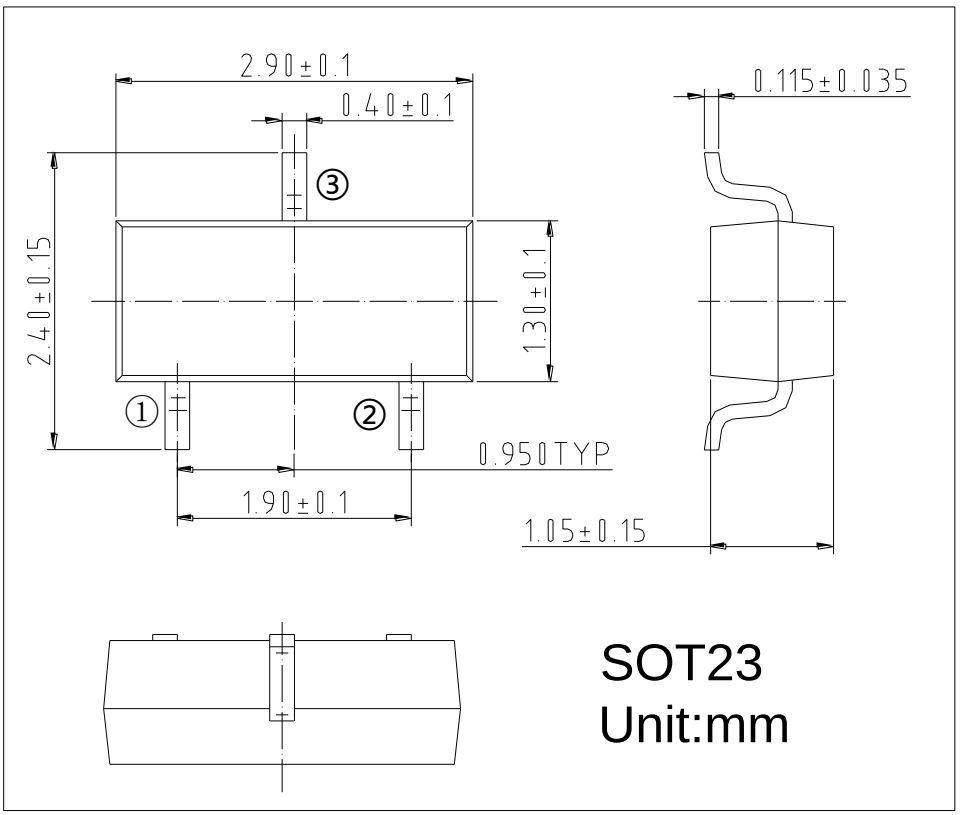
On-Resistance vs. Gate-to-Source Voltage (2.4 A)



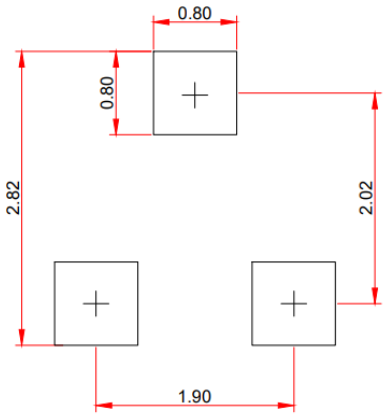
On-Resistance vs. Junction Temperature



➢ Package Information



Recommended Pad outline (Unit: mm)



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